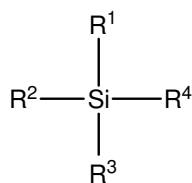


WHAT IS CLAIMED IS:

1. A composition for etching comprising:
 - a first inorganic acid;
 - 5 a first additive, being any one selected from the group consisting of phosphorous acid, an organic phosphite, a hypophosphite, and mixtures thereof; and
 - a solvent.
- 10 2. The composition for etching according to claim 1, wherein the first inorganic acid is any one selected from the group consisting of sulfuric acid, nitric acid, phosphoric acid, silicic acid, hydrofluoric acid, boric acid, hydrochloric acid, perchloric acid, and mixtures thereof.
- 15 3. The composition for etching according to claim 1, wherein the organic phosphite is any one alkyl phosphite selected from the group consisting of dimethyl phosphite, diethyl phosphite, dipropyl phosphite, diisopropyl phosphite, dibutyl phosphite, trimethyl phosphite, triethyl phosphite, tripropyl phosphite, triisopropyl phosphite, tributyl phosphite, diphenyl phosphite, dibenzyl phosphite, and mixtures thereof.
- 20 4. The composition for etching according to claim 1, wherein the hypophosphite is any one selected from the group consisting of ammonium hypophosphite, sodium hypophosphite, potassium hypophosphite, and mixtures thereof.
- 25 5. The composition for etching according to claim 1, wherein the composition for etching comprises the first additive at a proportion of 0.01% to 15% by weight, the first inorganic acid at a proportion of 70% to 99% by weight, and the solvent as the balance.

6. The composition for etching according to claim 1, further comprising a second additive including a silane inorganic acid salt produced by reacting a second inorganic acid with a silane compound.

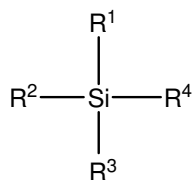
7. The composition for etching according to claim 6, wherein the silane inorganic acid salt is a silane inorganic acid salt produced by reacting any one second inorganic acid selected from the group consisting of sulfuric acid, fuming sulfuric acid, nitric acid, phosphoric acid, anhydrous phosphoric acid, and mixtures thereof, with a silane compound represented by the following Chemical Formula 10:



[Chemical Formula 10]

wherein in Chemical Formula 10, R^1 to R^4 each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms; and at least any one of R^1 to R^4 represents a halogen atom or an alkoxy group having 1 to 10 carbon atoms.

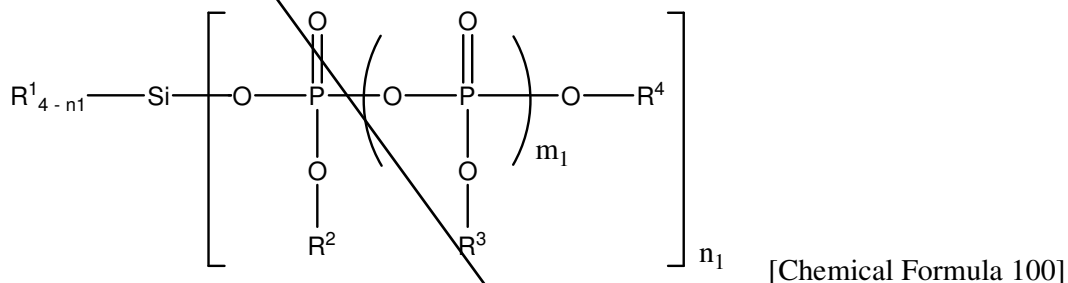
8. The composition for etching according to claim 6, wherein the silane inorganic acid salt is a silane inorganic acid salt produced by reacting a second organic acid including polyphosphoric acid, with a silane compound represented by the following Chemical Formula 10:



[Chemical Formula 10]

wherein in Chemical Formula 10, R¹ to R⁴ each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms; and at least any one of R¹ to R⁴ represents a halogen atom or an alkoxy group having 1 to 10 carbon atoms.

9. The composition for etching according to claim 8, wherein the silane inorganic acid salt includes a compound represented by the following Chemical Formula 100:



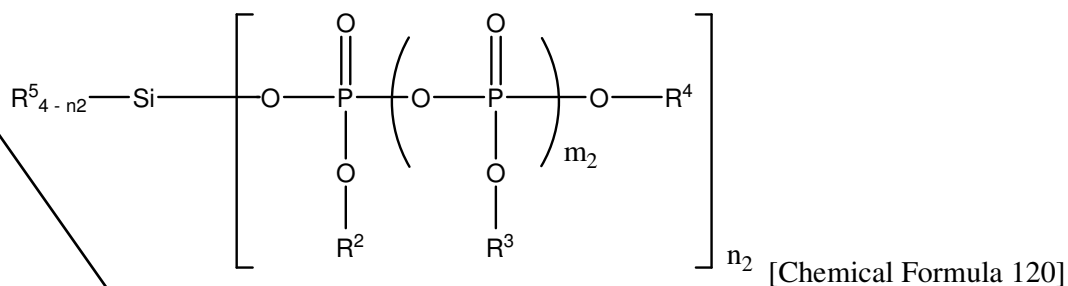
wherein in Chemical Formula 100, R¹ represents any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

n₁ represents an integer from 1 to 4;

m₁ represents an integer from 1 to 10; and

R² to R⁴ each represent a hydrogen atom.

10. The composition for etching according to claim 9, wherein in the silane inorganic acid salt represented by Chemical Formula (100), any one hydrogen atom selected from the group consisting of R² to R⁴ is substituted by a substituent represented by the following Chemical Formula 120:



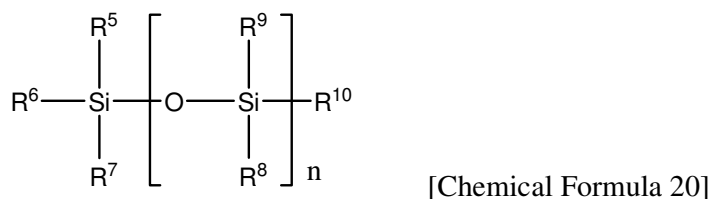
wherein in Chemical Formula 120, any one of R⁵'s represents a linking group linked to a structure represented by Chemical Formula 100, while the others each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

R² to R⁴ each independently represent a hydrogen atom or is substituted by a second substituent represented by Chemical Formula 120;

n₂ represents an integer from 0 to 3; and

m₂ represents an integer from 1 to 10.

11. The composition for etching according to claim 6, wherein the silane inorganic acid salt is a siloxane inorganic acid salt produced by reacting any one second inorganic acid selected from the group consisting of phosphoric acid, anhydrous phosphoric acid, pyrophosphoric acid, polyphosphoric acid, and mixtures thereof, with a siloxane compound represented by the following Chemical Formula 20:



wherein in Chemical Formula 20, R⁵ to R¹⁰ each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl

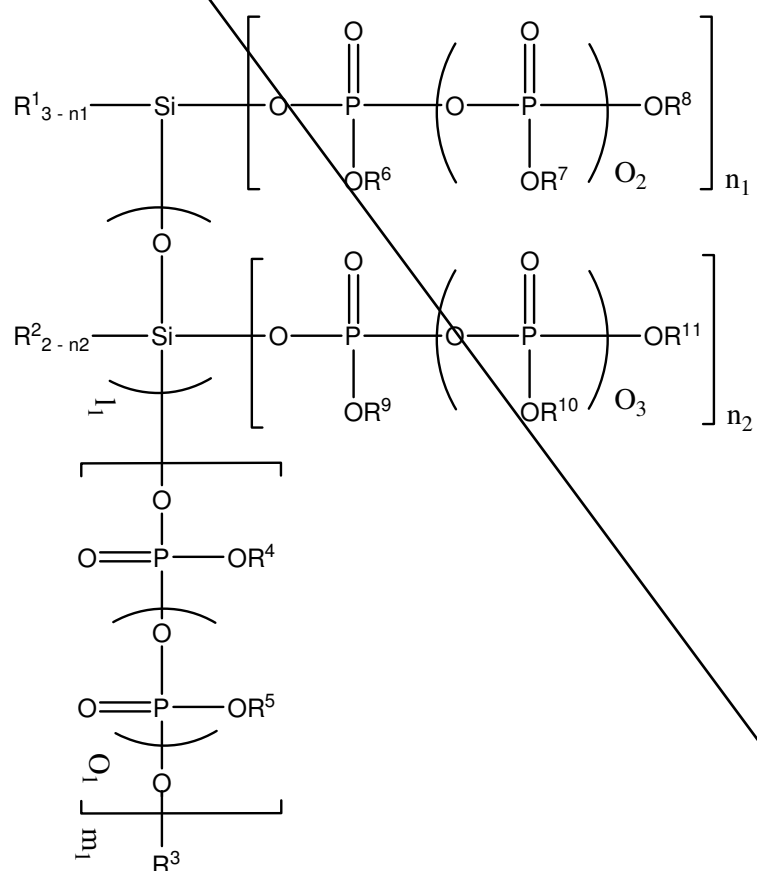
group having 6 to 30 carbon atoms;

at least any one of R^5 to R^{10} represents a halogen atom or an alkoxy group having 1 to 10 carbon atoms; and

n represents an integer from 1 to 10.

5

12. The composition for etching according to claim 11, wherein the siloxane inorganic acid salt includes a compound represented by the following Chemical Formula 200:



[Chemical Formula 200]

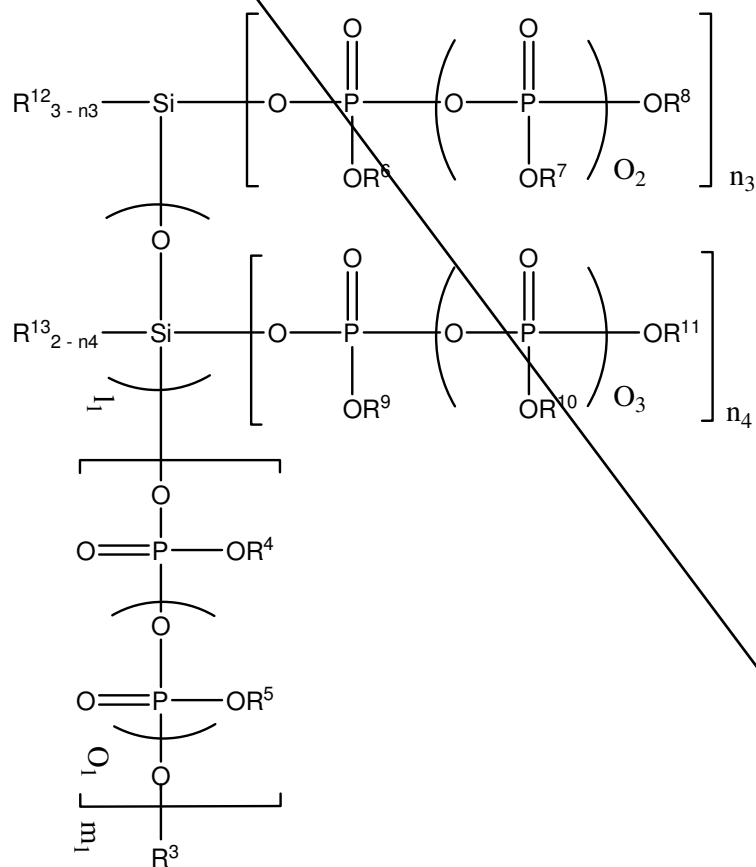
wherein in Chemical Formula 200, R^1 and R^2 each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

n_1 represents an integer from 0 to 3; n_2 represents an integer from 0 to 2; m_1

10

represents an integer of 0 or 1; the relation: $n_1+n_2+m_1 \geq 1$ is satisfied, l_1 represents an integer from 1 to 10; o_1 to o_3 each independently represent an integer from 0 to 10; and R^3 to R^{11} each represent a hydrogen atom.

- 5 13. The composition for etching according to claim 12, wherein in the siloxane inorganic acid salt represented by Chemical Formula 200, any one hydrogen atom selected from the group consisting of R^3 to R^{11} is substituted by a substituent represented by the following Chemical Formula 220:



[Chemical Formula 220]

- 10 wherein in Chemical Formula 220, any one of R^{12} 's and R^{13} 's represents a linking group linked to a structure represented by Chemical Formula 200, while the others each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10

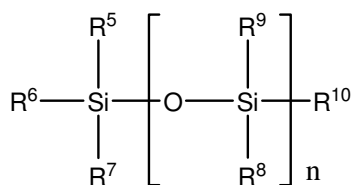
carbon atoms, and an aryl group having 6 to 30 carbon atoms;

R³ to R¹¹ each independently represent a hydrogen atom or is substituted by a second substituent represented by Chemical Formula 220;

n₃ represents an integer from 0 to 3; n₄ represents an integer from 0 to 2; m₁

5 represents an integer of 0 or 1; l₁ represents an integer from 1 to 10; and o₁ to o₃ each independently represent an integer from 0 to 10.

14. The composition for etching according to claim 6, wherein the silane inorganic acid salt is a siloxane inorganic acid salt produced by reacting any one second inorganic acid
10 selected from the group consisting of sulfuric acid, fuming sulfuric acid, and a mixture thereof, with a siloxane compound represented by the following Chemical Formula 20:



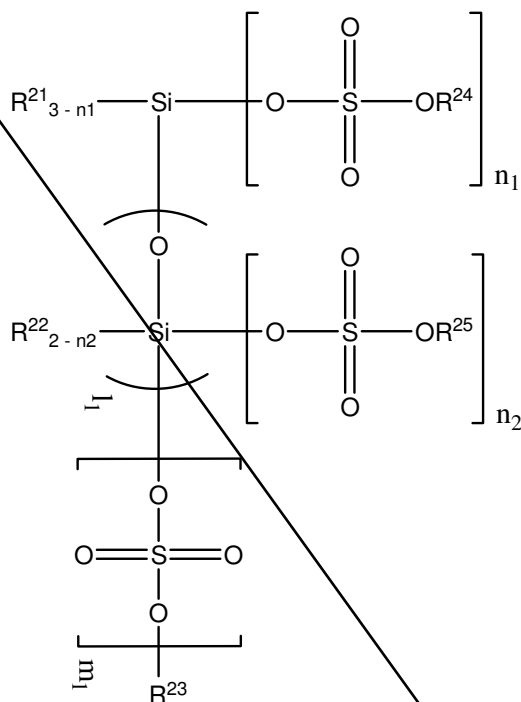
[Chemical Formula 20]

wherein in Chemical Formula 20, R⁵ to R¹⁰ each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group
15 having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

at least any one of R⁵ to R¹⁰ represents a halogen atom or an alkoxy group having 1 to 10 carbon atoms; and

n represents an integer from 1 to 10.

15. The composition for etching according to claim 14, wherein the siloxane inorganic acid salt includes a compound represented by the following Chemical Formula 230:



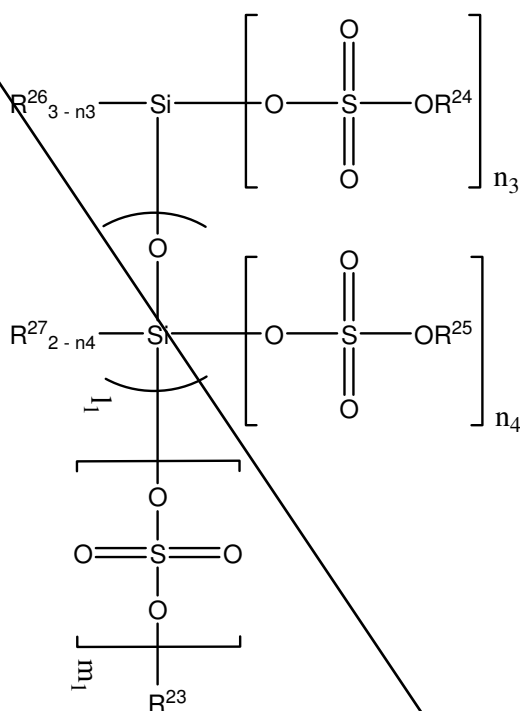
[Chemical Formula 230]

wherein in Chemical Formula 230, R^{21} and R^{22} each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

n_1 represents an integer from 0 to 3; n_2 represents an integer from 0 to 2; m_1 represents an integer of 0 or 1; the relation: $n_1+n_2+m_1 \geq 1$ is satisfied; l_1 represents an integer from 1 to 10; and

R^{23} to R^{25} each represent a hydrogen atom.

16. The composition for etching according to claim 15, wherein in the siloxane inorganic acid salt represented by Chemical Formula 230, any one hydrogen atom selected from the group consisting of R^{23} to R^{25} is substituted by a substituent represented by the following Chemical Formula 250:



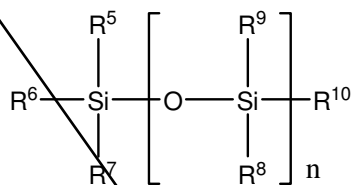
[Chemical Formula 250]

wherein in Chemical Formula 250, any one of R²⁶'s and R²⁷'s represents a linking group linked to a structure represented by Chemical Formula 230, while the others each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

R²³ to R²⁵ each independently represent a hydrogen atom or is substituted by a second substituent represented by Chemical Formula 250;

n₃ represents an integer from 0 to 3; n₄ represents an integer from 0 to 2; m₁ represents an integer of 0 or 1; and I₁ represents an integer from 1 to 10.

17. The composition for etching according to claim 6, wherein the silane inorganic acid salt is a siloxane inorganic acid salt produced by reacting a second inorganic acid including nitric acid, with a siloxane compound represented by the following Chemical Formula 20:



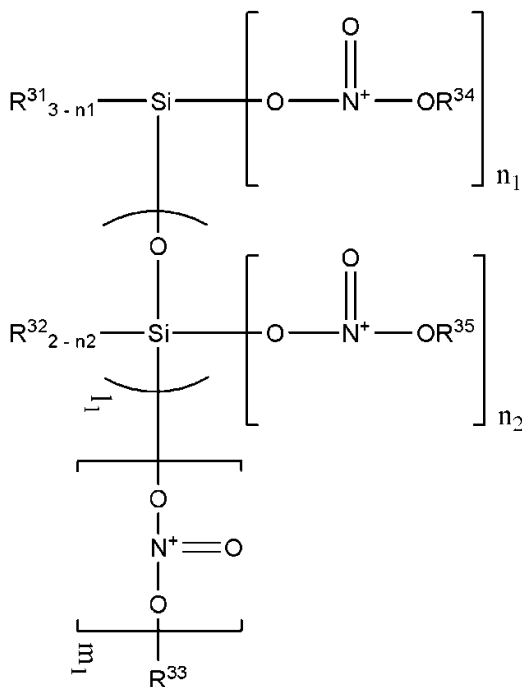
[Chemical Formula 20]

wherein in Chemical Formula 20, R⁵ to R¹⁰ each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

at least any one of R⁵ to R¹⁰ represents a halogen atom or an alkoxy group having 1 to 10 carbon atoms; and

n represents an integer from 1 to 10.

18. The composition for etching according to claim 17, wherein the siloxane inorganic acid salt includes a compound represented by the following Chemical Formula 260:



[Chemical Formula 260]

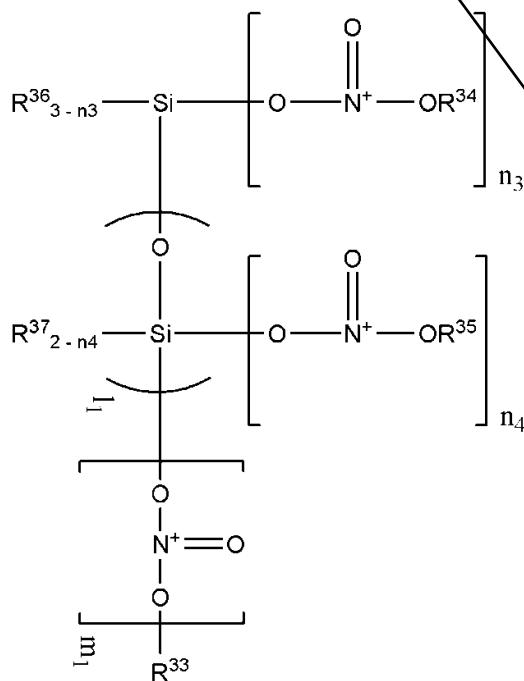
wherein in Chemical Formula 260, R³¹ and R³² each independently represent any

one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

n_1 represents an integer from 0 to 3; n_2 represents an integer from 0 to 2; m_1 represents an integer of 0 or 1; the relation: $n_1+n_2+m_1 \geq 1$ is satisfied, l_1 represents an integer from 1 to 10; and

R^{33} to R^{35} each represent a hydrogen atom.

19. The composition for etching according to claim 18, wherein in the siloxane inorganic acid salt represented by Chemical Formula 260, any one hydrogen atom selected from the group consisting of R^{33} to R^{35} is substituted by a substituent represented by the following Chemical Formula 280:



[Chemical Formula 280]

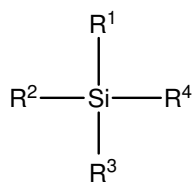
wherein in Chemical Formula 280, any one of R^{36} 's and R^{37} 's represents a linking group linked to a structure represented by Chemical Formula 260, while the others each independently represent any one selected from the group consisting of a hydrogen atom, a

halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

R^{33} to R^{35} each independently represent a hydrogen atom or is substituted by a second substituent represented by Chemical Formula 280;

5 n_3 represents an integer from 0 to 3; n_4 represents an integer from 0 to 2; m_1 represents an integer of 0 or 1; and l_1 represents an integer from 1 to 10.

20. The composition for etching according to claim 1, wherein the composition for etching further comprises a second additive including an alkoxysilane compound
10 represented by the following Chemical Formula 300:



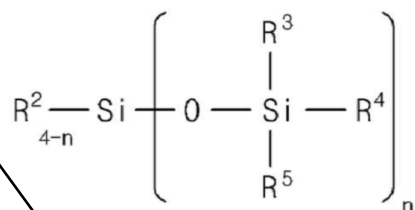
[Chemical Formula 300]

wherein in Chemical Formula 300, R^1 to R^4 each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, a hydroxyl group, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms,
15 an aminoalkyl group having 1 to 10 carbon atoms, an aminoalkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms; and

at least any one of R^1 to R^4 represents an alkoxy group having 1 to 10 carbon atoms, an aminoalkyl group having 1 to 10 carbon atoms, or an aminoalkoxy group having 1 to 10 carbon atoms.

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21. The composition for etching according to claim 1, wherein the composition for etching further comprises a second additive including a siloxane compound represented by the following Chemical Formula 350:



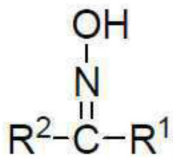
[Chemical Formula 350]

wherein in Chemical Formula 350, R^2 to R^5 each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, a hydroxyl group, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, an aminoalkyl group having 1 to 10 carbon atoms, an aminoalkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

at least any one of R^2 to R^5 represents an alkoxy group having 1 to 10 carbon atoms, an aminoalkyl group having 1 to 10 carbon atoms, or an aminoalkoxy group having 1 to 10 carbon atoms; and

n represents an integer from 1 to 4.

22. The composition for etching according to claim 1, wherein the composition for etching further comprises a second additive including an oxime compound represented by the following Chemical Formula 400:



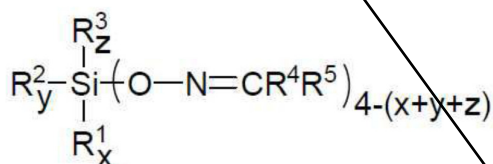
[Chemical Formula 400]

wherein in Chemical Formula 400, R^1 and R^2 each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 20 carbon atoms, an alkoxy group having 1 to 20 carbon atoms, an alkenyl group having 2 to 20 carbon atoms, a cycloalkyl group having 3 to 20 carbon atoms, an aminoalkyl group having 1 to 20 carbon atoms, an aryl group having 6 to 20 carbon atoms, an alkylcarbonyl group having 1 to 20 carbon atoms, an alkylcarbonyloxy group having 1

to 20 carbon atoms, and a cyanoalkyl group having 1 to 10 carbon atoms.

23 The composition for etching according to claim 22, wherein the oxime compound is any one selected from the group consisting of acetone oxime, 2-butanone oxime, 5 acetaldehyde oxime, cyclohexanone oxime, acetophenone oxime, cyclodecanone oxime, and mixtures thereof.

24. The composition for etching according to claim 1, wherein the composition for etching further comprises a second additive including an oxime silane compound 10 represented by the following Chemical Formula 500:



[Chemical Formula 500]

wherein in Chemical Formula 500, R^1 to R^3 each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 20 carbon atoms, an alkenyl group having 2 to 20 carbon atoms, a cycloalkyl 15 group having 3 to 20 carbon atoms, an aryl group having 6 to 20 carbon atoms, an arylalkyl group having 7 to 20 carbon atoms, and an alkylcarbonyl group having 1 to 20 carbon atoms;

R^4 and R^5 each independently represent any one selected from the group consisting of an alkyl group having 1 to 20 carbon atoms, a cycloalkyl group having 3 to 20 carbon 20 atoms, an aryl group having 6 to 20 carbon atoms, an arylalkyl group having 7 to 20 carbon atoms, and an alkylcarbonyl group having 1 to 20 carbon atoms, or R^4 and R^5 are bonded to each other as an alkylene group having 3 to 12 carbon atoms and form an alicyclic ring;

x, y, and z each independently represent an integer from 0 to 3, and $x+y+z$ 25 represents an integer from 0 to 3.

25. The composition for etching according to claim 24, wherein the oxime silane compound is any one selected from the group consisting of di(ethyl ketoxime)silane, mono(ethyl ketoxime)silane, tris(ethyl ketoxime)silane, tetra(ethyl ketoxime)silane, methyl tris(methyl ethyl ketoxime)silane, methyl tris(acetoxime)silane, methyl tris(methyl isobutyl ketoxime)silane, dimethyl di(methyl ethyl ketoxime)silane, trimethyl (methyl ethyl ketoxime)silane, tetra(methyl ethyl ketoxime)silane, tetra(methyl isobutyl ketoxime)silane, vinyl tris(methyl ethyl ketoxime)silane, methyl vinyl di(methyl ethyl ketoxime)silane, vinyl tris(methyl isobutyl ketoxime)silane, and phenyl tris(methyl ethyl ketoxime)silane.

26. The composition for etching according to any one of claims 6 to 25, wherein the composition for etching includes the second additive at a proportion of 0.01% to 20% by weight with respect to the total amount of the composition for etching.

27. The composition for etching according to claim 1, wherein the composition for etching further comprises an ammonium-based compound at a proportion of 0.01% to 20% by weight with respect to the total amount of the composition for etching.

28. The composition for etching according to claim 27, wherein the ammonium-based compound is any one selected from the group consisting of an aqueous ammonia solution, ammonium chloride, ammonium acetate, ammonium phosphate, ammonium peroxydisulfate, ammonium sulfate, ammonium hydrofluoride, and mixtures thereof.

29. The composition for etching according to claim 1, wherein the composition for etching further comprises a fluorine-based compound at a proportion of 0.01% to 1% by weight with respect to the total amount of the composition for etching.

30. The composition for etching according to claim 29, wherein the fluorine-based compound is any one selected from the group consisting of hydrogen fluoride, ammonium fluoride, ammonium hydrogen fluoride, and mixtures thereof.

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31. A method of manufacturing a semiconductor device, the method comprising an etching process carried out by using the composition for etching according to claim 1.

32. The method according to claim 31, wherein the etching process involves selective
10 etching of a nitride film with respect to an oxide film, and
the nitride film etching process is carried out at a temperature of from 50°C to 300°C.

WHAT IS CLAIMED IS:

1. A composition for silicon-nitride-film etching comprising:

phosphoric acid as a first inorganic acid;

a first additive, being any one selected from the group consisting of phosphorous acid, an organic phosphite, a hypophosphite, and mixtures thereof; and

a solvent.

2. The composition for silicon-nitride-film etching according to claim 1, wherein the organic phosphite is an alkyl phosphite, being any one selected from the group consisting of dimethyl phosphite, diethyl phosphite, dipropyl phosphite, diisopropyl phosphite, dibutyl phosphite, trimethyl phosphite, triethyl phosphite, tripropyl phosphite, triisopropyl phosphite, tributyl phosphite, diphenyl phosphite, dibenzyl phosphite, and mixtures thereof.

3. The composition for silicon-nitride-film etching according to claim 1, wherein the hypophosphite is any one selected from the group consisting of ammonium hypophosphite, sodium hypophosphite, potassium hypophosphite, and mixtures thereof.

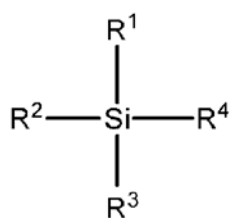
4. The composition for silicon-nitride-film etching according to claim 1, comprising the first additive at a proportion of 0.01% to 15% by weight, the first inorganic acid at a proportion of 70% to 99% by weight, and the solvent as the balance.

5. The composition for silicon-nitride-film etching according to claim 1, comprising a second additive, being any one selected from silane inorganic acid salt, alkoxysilane compound, siloxane compound, oxime compound, oxime silane compound, and mixtures thereof.

6. The composition for silicon-nitride-film etching according to claim 1, wherein the silane inorganic acid salt is a silane inorganic acid salt produced by reacting any one second inorganic acid, which is selected from the group consisting of sulfuric acid, fuming sulfuric acid, nitric acid, phosphoric acid, anhydrous phosphoric acid, pyrophosphoric acid, polyphosphoric acid and mixtures thereof, with a silane compound represented by following Chemical Formula 10:

<Chemical Formula 10>

[Chemical Formula 1]



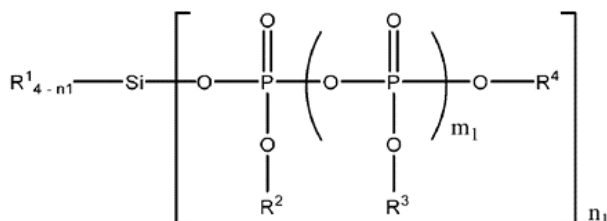
wherein, in Chemical Formula 10,

R1 to R4 each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms; and at least any one of R1 to R4 represents a halogen atom or an alkoxy group having 1 to 10 carbon atoms.

7. The composition for silicon-nitride-film etching according to claim 6, wherein the silane inorganic acid salt comprises a compound represented by following Chemical Formula 100:

<Chemical Formula 100>

[Chemical Formula 2]



wherein, in Chemical Formula 100,

R1 represents any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

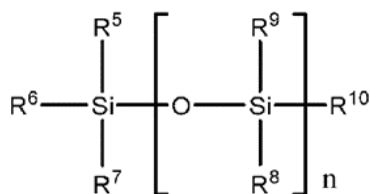
n1 represents an integer from 1 to 4; m1 represents an integer from 1 to 10; and

R2 to R4 each independently represent a hydrogen atom.

8. The composition for silicon-nitride-film etching according to claim 5, wherein the silane inorganic acid salt is a siloxane inorganic acid salt produced by reacting a second inorganic, which is selected from the group consisting of sulfuric acid, fuming sulfuric acid, nitric acid, phosphoric acid, anhydrous phosphoric acid, pyrophosphoric acid, polyphosphoric acid and mixtures thereof, with a siloxane compound represented by following Chemical Formula 20:

<Chemical Formula 20>

[Chemical Formula 3]



wherein, in Chemical Formula 20,

R5 to R10 each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

at least any one of R5 to R10 represents a halogen atom or an alkoxy group having 1 to 10 carbon atoms; and

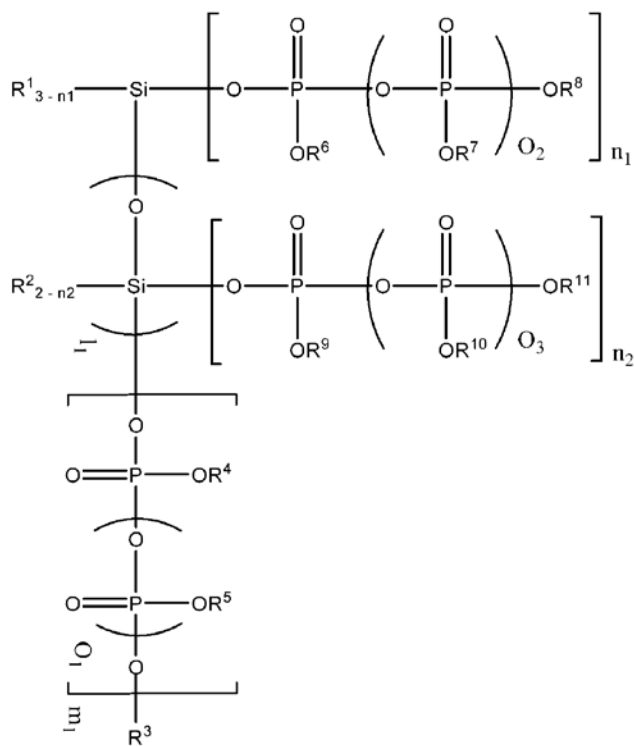
n represents an integer from 1 to 10.

9. The composition for silicon-nitride-film etching according to claim 8, wherein the silane inorganic

acid salt includes a compound represented by the following Chemical Formula 200:

<Chemical Formula 200>

[Chemical Formula 4]

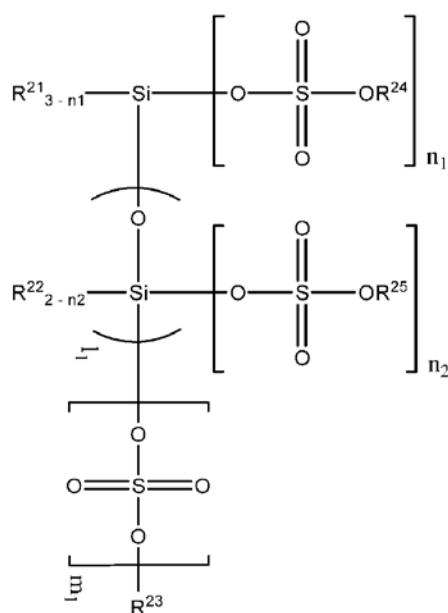


- 5 wherein, in Chemical Formula 200,
- R1 and R2 each independently represents any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;
- n1 represents an integer from 0 to 3; n2 represents an integer from 0 to 2; m1 represents an integer of 0 or 1; the relation: $n1+n2+m1 \geq 1$ is satisfied, l_1 represents an integer from 1 to 10;
- 10 o1 to o3 each independently represent an integer from 0 to 10; and
- R3 to R11 each independently represent a hydrogen atom.

10. The composition for silicon-nitride-film etching according to claim 8, wherein the siloxane
- 15 inorganic acid salt includes a compound represented by the following Chemical Formula 230:

<Chemical Formula 230>

[Chemical Formula 5]



wherein, in Chemical Formula 230,

R²¹ and R²² each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

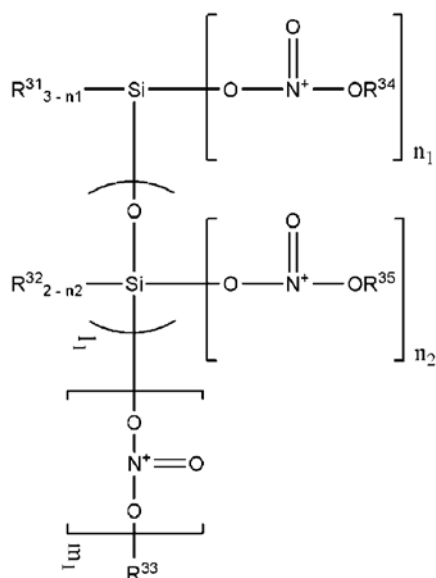
n₁ represents an integer from 0 to 3; n₂ represents an integer from 0 to 2; m₁ represents an integer of 0 or 1; the relation: n₁+n₂+m₁≥1 is satisfied; l₁ represents an integer from 1 to 10; and

R²³ to R²⁵ each independently represent a hydrogen atom.

11. The composition for silicon-nitride-film etching according to claim 8, wherein the siloxane inorganic acid salt includes a compound represented by the following Chemical Formula 260:

<Chemical Formula 260>

[Chemical Formula 6]



wherein in Chemical Formula 260,

R31 and R32 each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms;

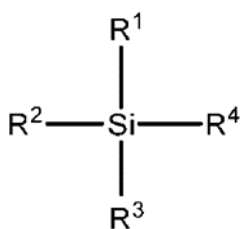
n1 represents an integer from 0 to 3; n2 represents an integer from 0 to 2; m1 represents an integer of 0 or 1; the relation: $n_1+n_2+m_1 \geq 1$ is satisfied, l₁ represents an integer from 1 to 10; and

R33 to R35 each independently represent a hydrogen atom.

12. The composition for silicon-nitride-film etching according to claim 8, wherein the alkoxysilane compound includes a compound represented by the following Chemical Formula 300:

<Chemical Formula 300>

[Chemical Formula 7]



wherein in Chemical Formula 300,

R1 to R4 each independently represent any one selected from the group consisting of a hydrogen

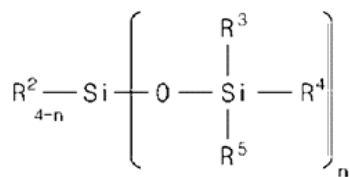
atom, a halogen atom, a hydroxyl group, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, an aminoalkyl group having 1 to 10 carbon atoms, an aminoalkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms; and

at least any one of R₁ to R₄ represents an alkoxy group having 1 to 10 carbon atoms, an aminoalkyl group having 1 to 10 carbon atoms, or an aminoalkoxy group having 1 to 10 carbon atoms.

13. The composition for silicon-nitride-film etching according to claim 5, wherein the siloxane compound includes a compound represented by the following Chemical Formula 350:

<Chemical Formula 350>

[Chemical Formula 8]



wherein in Chemical Formula 350,

R₂ to R₅ each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, a hydroxyl group, an alkyl group having 1 to 10 carbon atoms, an alkoxy group having 1 to 10 carbon atoms, an aminoalkyl group having 1 to 10 carbon atoms, an aminoalkoxy group having 1 to 10 carbon atoms, and an aryl group having 6 to 30 carbon atoms; at least any one of R₂ to R₅ represents an alkoxy group having 1 to 10 carbon atoms, an aminoalkyl group having 1 to 10 carbon atoms, or an aminoalkoxy group having 1 to 10 carbon atoms; and

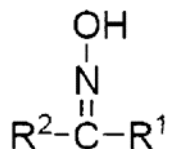
n represents an integer from 1 to 4.

14. The composition for silicon-nitride-film etching according to claim 5, wherein the oxime

compound includes a compound represented by the following Chemical Formula 400:

<Chemical Formula 400>

[Chemical Formula 9]



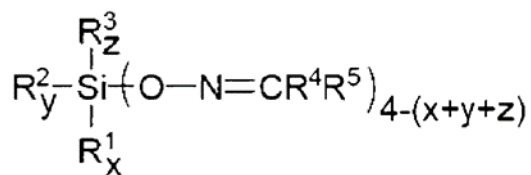
wherein, in Chemical Formula 400,

R¹ and R² each independently represent any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 20 carbon atoms, an alkoxy group having 1 to 20 carbon atoms, an alkenyl group having 2 to 20 carbon atoms, a cycloalkyl group having 3 to 20 carbon atoms, an aminoalkyl group having 1 to 20 carbon atoms, an aryl group having 6 to 20 carbon atoms, an alkylcarbonyl group having 1 to 20 carbon atoms, an alkylcarbonyloxy group having 1 to 20 carbon atoms, and a cyanoalkyl group having 1 to 10 carbon atoms.

15. The composition for silicon-nitride-film etching according to claim 5, wherein the oxime silane compound includes a compound represented by the following Chemical Formula 500:

<Chemical Formula 500>

[Chemical Formula 10]



wherein, in Chemical Formula 500,

R¹ to R³ each independently represents any one selected from the group consisting of a hydrogen atom, a halogen atom, an alkyl group having 1 to 20 carbon atoms, an alkenyl group having 2 to 20 carbon atoms, a cycloalkyl group having 3 to 20 carbon atoms, an aryl group having 6 to 20 carbon atoms, an arylalkyl group having 7 to 20 carbon atoms, and an alkylcarbonyl group having

1 to 20 carbon atoms;

R4 and R5 each independently represents any one selected from the group consisting of an alkyl group having 1 to 20 carbon atoms, a cycloalkyl group having 3 to 20 carbon atoms, an aryl group having 6 to 20 carbon atoms, an arylalkyl group having 7 to 20 carbon atoms, and an alkylcarbonyl group having 1 to 20 carbon atoms, or R4 and R5 are bonded to each other, as the alkylene groups having 3 to 12 carbon atoms, to form an alicyclic ring;

x, y, and z each independently represents an integer from 0 to 3, and x+y+z represents an integer from 0 to 3.

16. The composition for silicon-nitride-film etching according to claim 5, comprising the second additive at a proportion of 0.01% to 20% by weight with respect to the total amount of the composition for etching.

17. The composition for silicon-nitride-film etching according to claim 1, comprising an ammonium-based compound at a proportion of 0.01% to 20% by weight and/or a fluorine-based compound at a proportion of 0.01% to 1% by weight, with respect to the total amount of the composition.

18. A method of manufacturing a semiconductor device, the method comprising a silicon-nitride-film etching process carried out by using the composition for silicon-nitride-film etching according to claim 1.

19. The method according to claim 18, wherein the silicon-nitride-film etching process involves selective etching of a nitride film relative to an oxide film, and the silicon-nitride-film etching process is carried out at a temperature of from 50°C to 300°C.